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INFORMATION DISCLOSURE			LOSURE	Application Number	10/538,739	1
	STATEMENT BY APPLICANT			Filing Date	12/15/2003	/ %
	Date Submitted: April 6, 2009			First Named Inventor	Yasuhiro OKAMOT	O APR 06 2009
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			necessary)	Examiner Name	Sarah Kate Salerno	6
Sheet	1	of	1	Attorney Docket Number	029437-0108	A THADEMARK

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UNPUBLISHED U.S. PATENT APPLICATION DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Application Document Serial Number-Kind Code ² (if known)	Filing Date of Cited Document MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No.1	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ⁵ (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Т6		
	C1	JP 2001-230263A	08-24-2001	NEC CORP.		Α		
	C2	JP 2000-353708A	12-19-2000	NEC CORP.		Α		
	C3	JP 09-027505	01-28-1997	NIPPONDENSO CO. LTD.		Α		
	C4	JP 08-083813	03-26-1996	MITSUBISHI ELECTRIC		Α		
	C5	JP 02-072667	03-12-1990	TOSHIBA CORP.		Α		

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	Τ6	
	C6	Shawn T. Bradley et al., "Influence of A1GaN Deep Level Defects on A1GaN/GaN 2-DEG Carrier Confinement," IEEE Transactions on Electron Devices, Vol. 48:3, March 2001, 7 pages.		
	C7	J. LI et al, "High Breakdown Voltage GaN HFET With Field Plate," Electronic Letters, February 1, 2001, Vol. 37:3, pp. 196-197.		

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Examiner Signature	/Sarah Salerno/	Date Considered	11/18/2009

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

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